



ZXTP25020DZ 20V PNP high gain transistor in SOT89

Summary

$BV_{CEO} > -20V$

$BV_{ECO} > -4V$

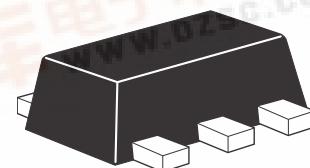
$I_{C(\text{cont})} = 5A$

$V_{CE(\text{sat})} < -65mV @ -1A$

$R_{CE(\text{sat})} = 39m\Omega$

$P_D = 2.4W$

Complementary part number ZXTN25020DZ

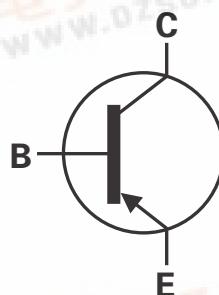


Description

Packaged in the SOT89 outline this new low saturation 20V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions

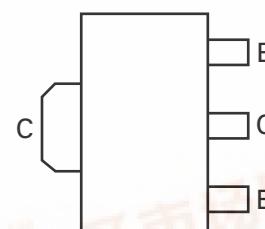
Features

- High peak current
- Low saturation voltage
- High gain
- SOT89 package



Applications

- DC-DC converters
- Load switch
- Motor drive
- Disconnect switch
- MOSFET and IGBT gate drive



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25020DZTA	7	12	1000

Device marking

- 1L5

ZXTP25020DZ

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-Base voltage	V_{CBO}	-25	V
Collector-Emitter voltage	V_{CEO}	-20	V
Emitter-Base voltage (reverse blocking)	V_{ECO}	-4	V
Emitter-Base voltage	V_{EBO}	-7	V
Continuous Collector current ^(c)	I_C	-5	A
Base current	I_B	-1	A
Peak pulse current	I_{CM}	-10	A
Power dissipation at $T_A = 25^\circ\text{C}$ ^(a)	P_D	1.1	W
Linear derating factor		8.8	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(b)	P_D	1.8	W
Linear derating factor		14.4	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(c)	P_D	2.4	W
Linear derating factor		19.2	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_A = 25^\circ\text{C}$ ^(d)	P_D	4.46	W
Linear derating factor		35.7	$\text{mW}/^\circ\text{C}$
Power dissipation at $T_C = 25^\circ\text{C}$ ^(e)	P_D	15.7	W
Linear derating factor		126	$\text{mW}/^\circ\text{C}$
Operating and storage temperature range	T_j, T_{stg}	-55 to 150	°C

Thermal resistance

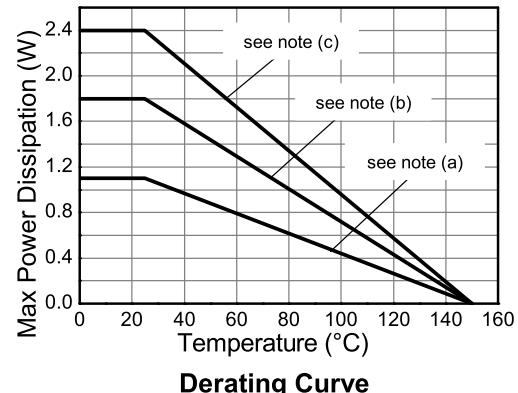
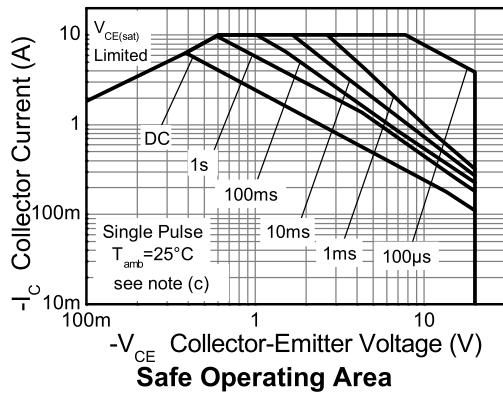
Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	117	$^\circ\text{C}/\text{W}$
Junction to ambient ^(b)	$R_{\Theta JA}$	68	$^\circ\text{C}/\text{W}$
Junction to ambient ^(c)	$R_{\Theta JA}$	51	$^\circ\text{C}/\text{W}$
Junction to ambient ^(d)	$R_{\Theta JA}$	28	$^\circ\text{C}/\text{W}$
Junction to case ^(e)	$R_{\Theta JC}$	7.95	$^\circ\text{C}/\text{W}$

NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (d) As (c) above measured at $t < 5$ seconds.
- (e) Junction to case (collector tab). Typical.

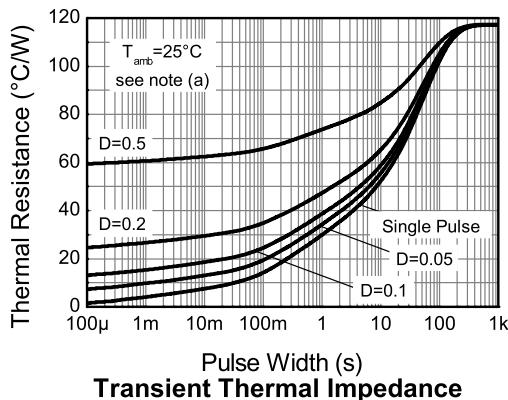
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Thermal characteristics

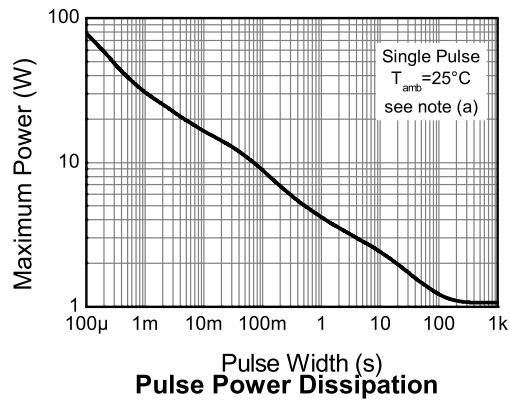


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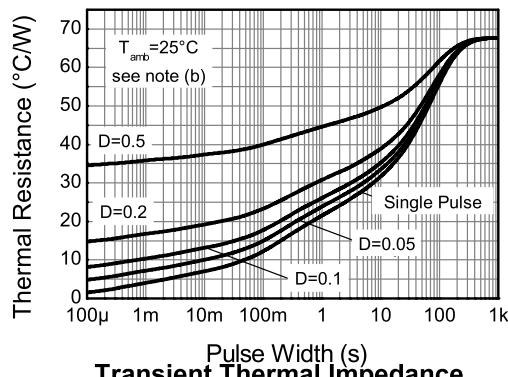
Thermal characteristics



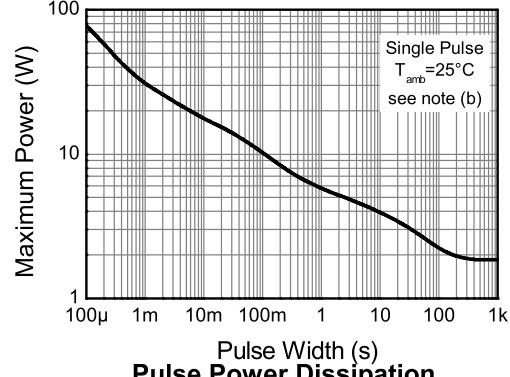
Transient Thermal Impedance



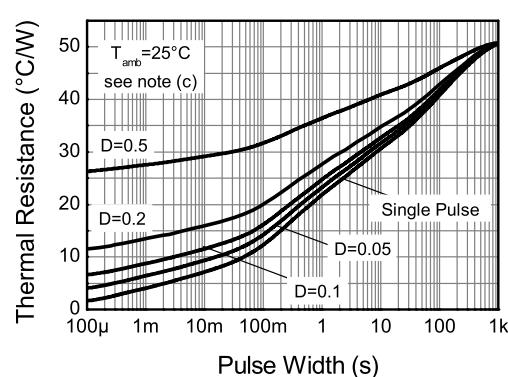
Pulse Power Dissipation



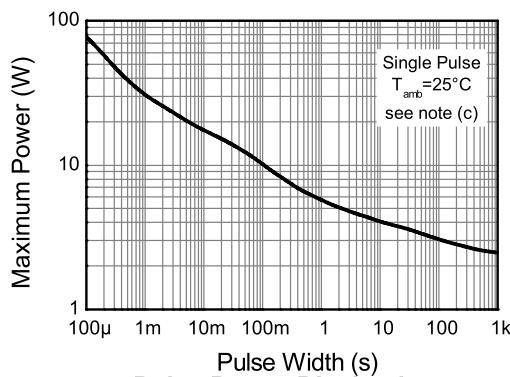
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



Pulse Power Dissipation

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Electrical characteristics (at $T_{amb} = 25^\circ C$ unless otherwise stated)

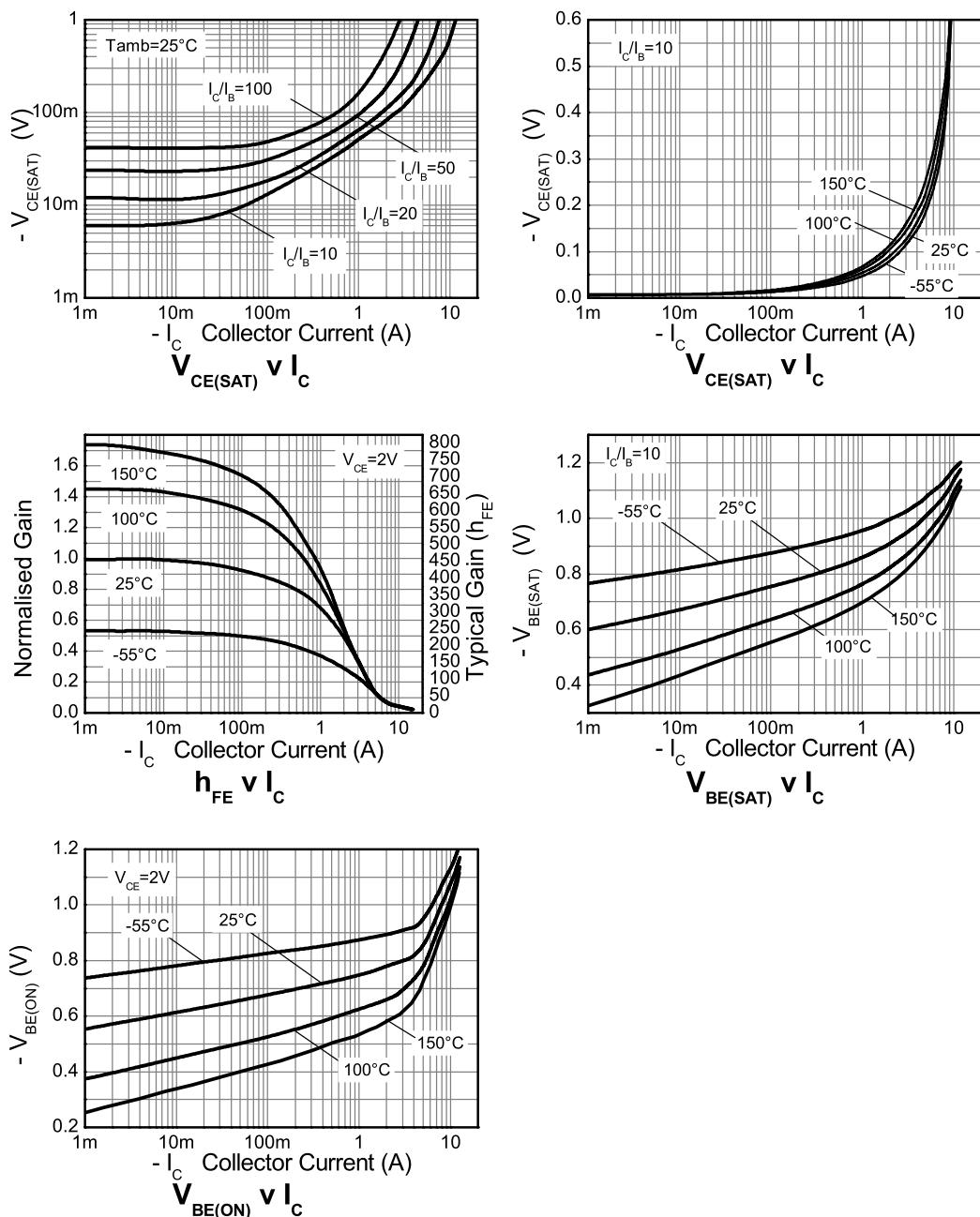
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base breakdown voltage	BV_{CBO}	-25	-55		V	$I_C = -100\mu A$
Collector-Emitter breakdown voltage	BV_{CEO}	-20	-45		V	$I_C = -10mA$ (*)
Emitter-Collector breakdown voltage (reverse blocking)	BV_{ECX}	-4	-8.5		V	$I_E = -100\mu A, R_{BC} < 1k\Omega$ or $0.25V > V_{BC} > -0.25V$
Emitter-Collector breakdown voltage (reverse blocking)	BV_{ECO}	-4	-8.5		V	$I_E = -100\mu A$
Emitter-Base breakdown voltage	BV_{EBO}	-7	-8.3		V	$I_E = -5.6V$
Collector-Base cut-off current	I_{CBO}		<1	-50 -0.5	nA μA	$V_{CB} = -25V$ $V_{CB} = -25V, T_{amb}=100^\circ C$
Emitter cut-off current	I_{EBO}		<1	-50	nA	$V_{EB} = -5.6V$
Collector-Emitter saturation voltage	$V_{CE(sat)}$		-50 -150 -185 -195	-65 -215 -245 -265	mV mV mV mV	$I_C = -1A, I_B = -100mA$ (*) $I_C = -1A, I_B = -10mA$ (*) $I_C = -2A, I_B = -40mA$ (*) $I_C = -5A, I_B = -500mA$ (*)
Base-Emitter saturation voltage	$V_{BE(sat)}$		-1010	-1100	mV	$I_C = -5A, I_B = -500mA$ (*)
Base-Emitter turn-on voltage	$V_{BE(on)}$		-870	-1000	mV	$I_C = -5A, V_{CE} = -2V$ (*)
Static forward current transfer ratio	h_{FE}	300 200 45	450 310 85 20	900		$I_C = -10mA, V_{CE} = -2V$ (*) $I_C = -1A, V_{CE} = -2V$ (*) $I_C = -5A, V_{CE} = -2V$ (*) $I_C = -10A, V_{CE} = -2V$ (*)
Transition frequency	f_T		290		MHz	$I_C = -50mA, V_{CE} = -10V$ $f = 100MHz$
Input capacitance	C_{ibo}		157	400	pF	$V_{EB} = -0.5V, f = 1MHz$ (*)
Output capacitance	C_{obo}		21	30	pF	$V_{CB} = -10V, f = 1MHz$ (*)
Delay time	t_d		14.2		ns	$V_{CC} = -10V, I_C = -1A,$ $I_{B1} = -I_{B2} = -50mA$
Rise time	t_r		16.3		ns	
Storage time	t_s		186		ns	
Fall time	t_f		32.7		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

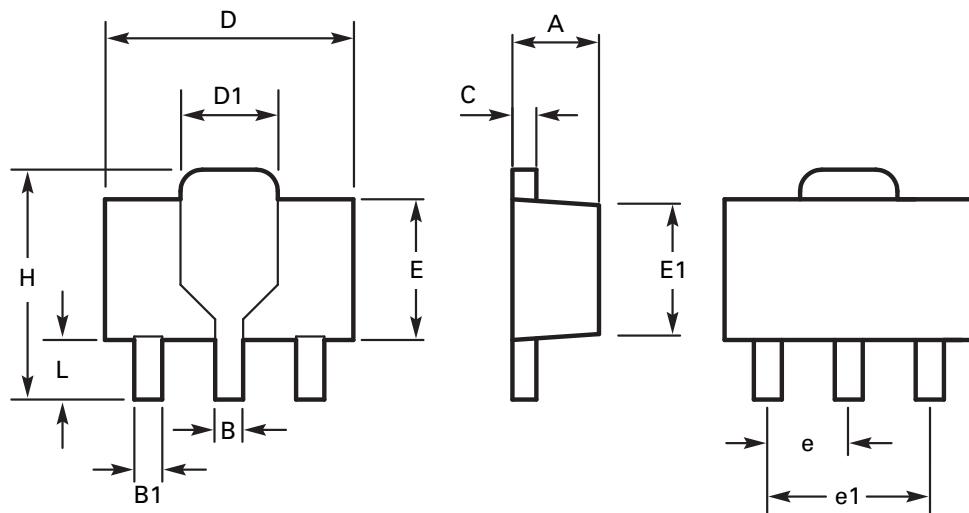
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Typical characteristics



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Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.52	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

ZXTP25020DZ

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